



Under 37 C.F.R. § 1.116
Expedited Procedure
Group Art Unit 2814

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

#7B M. Bawson
8/12/02

In re PATENT APPLICATION OF

Confirmation No.: 2698

SHIBATA

Group Art Unit: 2814

Appln. No.: 09/493,819

Examiner: D. WILLE

Filed: January 28, 2000

Title: GROUP III NITRIDE COMPOUND

February 26, 2002

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AMENDMENT AFTER FINAL UNDER 37 C.F.R. § 1.116

Hon. Commissioner of Patents
Washington, D.C. 20231

RECEIVED
FEB 28 2002
TECHNOLOGY CENTER 2800

Sir:

In response to the Office Action dated November 26, 2001, please amend the above-identified application as follows:

IN THE CLAIMS:

Please enter the following amended claims:

1. (Twice Amended) A group III nitride compound semiconductor device of a successively laminated structure comprising:
- a substrate;
 - a buffer layer;
 - a first layer formed of $\text{In}_x\text{Ga}_{1-x}\text{N}$ ($0 < x < 1$); and
 - a second layer formed of $\text{In}_y\text{Ga}_{1-y}\text{N}$ ($0 < y < 1$, $y \neq x$);
- wherein a composition ratio of In in said first layer is changed continuously or intermittently in a direction toward the second layer side from the buffer layer side so that a composition of said first layer in a face brought into contact with said second layer becomes substantially equal to a composition of said second layer; and
- wherein said buffer layer is disposed between and in direct contact with both said substrate and said first layer, and said first layer is disposed between and in direct contact with both said buffer layer and said second layer.